Abstracts

High-Efficiency HBT MMIC Linear Power Amplifier for L-Band Personal Communications Systems

T. Yoshimasu, N. Tanba and S. Hara. "High-Efficiency HBT MMIC Linear Power Amplifier for L-Band Personal Communications Systems." 1994 Microwave and Guided Wave Letters 4.3 (Mar. 1994 [MGWL]): 65-67.

A heterojunction bipolar transistor (HBT) MMIC linear power amplifier is demonstrated for the 1.9 GHz Japanese Personal Handy Phone utilizing the pi/4 DQPSK modulation technique. At an operating voltage of only 3 V, an output power of 21 dBm and a power added efficiency of 35% are obtained along with a modulation vector error of 4.5% and an adjacent channel interference of -60 dBc in +/-600 kHz offset frequency bands.

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